## PNP Epitaxial Silicon Transistor

## BSR16

## PNP General Purpose Amplifier

- This Device Designed for Use as General Purpose Amplifier and Switches Requiring Collector Currents to 500 mA
- Sourced from Process 63
- See BCW68G for Characteristics


## ABSOLUTE MAXIMUM RATINGS

( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$, unless otherwise specified.)

| Symbol | Parameter | Value | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{V}_{\mathrm{CEO}}$ | Collector-Emitter Voltage | -60 | V |
| $\mathrm{~V}_{\mathrm{CBO}}$ | Collector-Base Voltage | -60 | V |
| $\mathrm{~V}_{\text {EBO }}$ | Emitter-Base Voltage | -5.0 | V |
| $\mathrm{I}_{\mathrm{C}}$ | Collector Current - Continuous | -800 | mA |
| $\mathrm{~T}_{\mathrm{J}}, \mathrm{T}_{\mathrm{ST}}$ | Operating and Storage Junction <br> Temperature Range | $-55 \sim+150$ | ${ }^{\circ} \mathrm{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. These ratings are based on a maximum junction temperature of $150^{\circ} \mathrm{C}$.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

THERMAL CHARACTERISTICS
( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$, unless otherwise specified)

| Symbol | Parameter | Max. | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{P}_{\mathrm{D}}$ | Total Device Dissipation <br>  <br>  <br> Derate above 25 $\mathrm{C}^{\circ} \mathrm{C}$ | 350 | mW |
| $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |  |  |  |
| $\mathrm{R}_{\theta J \mathrm{~A}}$ | Thermal Resistance, Junction to <br> Ambient | 357 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  |  |  |

3. Device mounted on FR-4 PCB $40 \mathrm{~mm} \times 40 \mathrm{~mm} \times 1.5 \mathrm{~mm}$.

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SOT-23 CASE 318BM

MARKING DIAGRAM

\&Y ON Semiconductor Logo
Specific Device Code
Designates Space
Date Code (Week)

PIN ASSIGNMENT


ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :--- | :---: | :---: |
| BSR16 | SOT-23 <br> (Pb-Free) | $3,000 /$ <br> Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS $\left(\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}\right.$, unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |  |  |
| BV ${ }_{\text {(BR) }}$ CeO | Collector-Emitter Breakdown Voltage | $\mathrm{I}_{\mathrm{C}}=-10 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=0$ | -60 |  |  | V |
| $\mathrm{BV}_{\text {( }{ }_{\text {BR }} \text { ) } \mathrm{CBO}}$ | Collector-Base Breakdown Voltage | $\mathrm{I}_{\mathrm{C}}=-100 \mu \mathrm{~A}, \mathrm{I}_{\mathrm{E}}=0$ | -60 |  |  | V |
| BV ${ }_{\text {(BR) }}$ EBO | Emitter-Base Breakdown Voltage | $\mathrm{I}_{\mathrm{E}}=-10 \mu \mathrm{~A}, \mathrm{I}_{\mathrm{C}}=0$ | -5.0 |  |  | V |
| $\mathrm{I}_{\text {cbo }}$ | Collector Cut-off Current | $\begin{aligned} & \mathrm{V}_{\mathrm{CB}}=-50 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{CB}}=-50 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=150^{\circ} \mathrm{C} \end{aligned}$ |  |  | $\begin{aligned} & -10 \\ & -10 \end{aligned}$ | $\begin{aligned} & \mathrm{nA} \\ & \mu \mathrm{~A} \end{aligned}$ |
| $I_{\text {CEX }}$ | Collector Cut-off Current | $\mathrm{V}_{\text {CE }}=-30 \mathrm{~V}, \mathrm{~V}_{\text {EB }}=-0.5 \mathrm{~V}$ |  |  | -50 | nA |
| $\mathrm{I}_{\text {BEX }}$ | Reverse Base Current | $\mathrm{V}_{\mathrm{CE}}=-30 \mathrm{~V}, \mathrm{~V}_{\mathrm{EB}}=-3.0 \mathrm{~V}$ |  |  | -50 | nA |

ON CHARACTERISTICS

| $\mathrm{h}_{\text {FE }}$ | DC Current Gain | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=-0.1 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-10 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{C}}=-1.0 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-10 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{C}}=-10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-10 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{C}}=-150 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-10 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{C}}=-500 \mathrm{VA}, \mathrm{~V}_{\mathrm{CE}} \end{aligned}$ | $\begin{gathered} 75 \\ 100 \\ 100 \\ 100 \\ 50 \end{gathered}$ | 300 |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {CE }}$ (sat) | Collector-Emitter Saturation Voltage | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=-150 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=-15 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{C}}=-500 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=-50 \mathrm{~mA} \end{aligned}$ |  |  | $\begin{aligned} & \hline-0.4 \\ & -1.6 \end{aligned}$ | V |
| $\mathrm{V}_{\mathrm{BE}}$ (sat) | Base-Emitter Saturation Voltage | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=-150 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=-15 \mathrm{~mA} \\ & \mathrm{I}_{\mathrm{C}}=-500 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=-50 \mathrm{~mA} \end{aligned}$ |  |  | $\begin{array}{r} \hline-1.3 \\ -2.6 \\ \hline \end{array}$ | V |

SMALL SIGNAL CHARACTERISTICS

| $\mathrm{f}_{\mathrm{T}}$ | Current Gain Bandwidth Product | $\mathrm{I}=-50 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=-20 \mathrm{~V}$, <br> $\mathrm{f}=100 \mathrm{MHz}, \mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | 200 |  |  |
| :---: | :--- | :--- | :--- | :--- | :--- |
| $\mathrm{C}_{\mathrm{cb}}$ | Output Capacitance | $\mathrm{V}_{\mathrm{CB}}=-10 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{f}=1.0 \mathrm{MHz}$ |  |  | 8.0 |
| $\mathrm{C}_{\mathrm{eb}}$ | Emitter-Base Capacitance | $\mathrm{V}_{\mathrm{CB}}=-2.0 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{f}=1.0 \mathrm{MHz}$ |  | pF |  |

SWITCHING CHARACTERISTICS


Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.


SOT-23
CASE 318BM
ISSUE A

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

| DIM | MILIMETERS |  |  |
| :--- | :---: | :---: | :---: |
|  | MIN. | NOM. | MAX. |
| A | --- | --- | 1.20 |
| A1 | 0.00 | 0.05 | 0.10 |
| A2 | 0.93 REF |  |  |
| b | 0.37 | 0.44 | 0.60 |
| c | 0.08 | 0.15 | 0.23 |
| D | 2.72 | 2.92 | 3.12 |
| E | 2.10 | 2.40 | 2.70 |
| E1 | 1.15 | 1.30 | 1.50 |
| e | 0.95 BSC |  |  |
| e1 | 1.90 BSC |  |  |
| L | 0.20 | --- | --- |
| L1 | 0.55 REF |  |  |
| z | 0.29 REF |  |  |

LAND PATTERN
RECOMMENDATION

## NOTES: UNLESS OTHERWISE SPECIFIED

A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 2009.
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " r ", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code
M = Date Code

- = Pb-Free Package


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| ---: | :--- | :--- | :--- |
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